

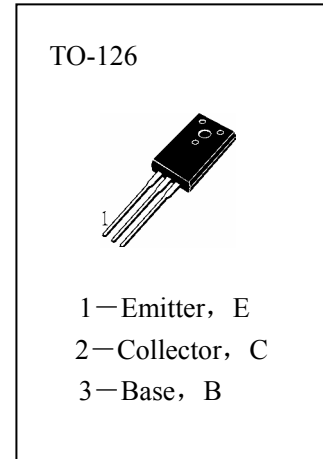
HS631K

APPLICATIONS

Low frequency power amplifier, Medium Seed switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation (T _c =25°C)	1W
V _{CB0}	Collector-Base Voltage	-120V
V _{CEO}	Collector-Emitter Voltage	-120V
V _{EBO}	Emitter-Base Voltage	-5V
I _C	Collector Current	-1A

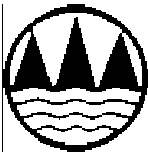


ELECTRICAL CHARACTERISTICS (T_a=25°C)

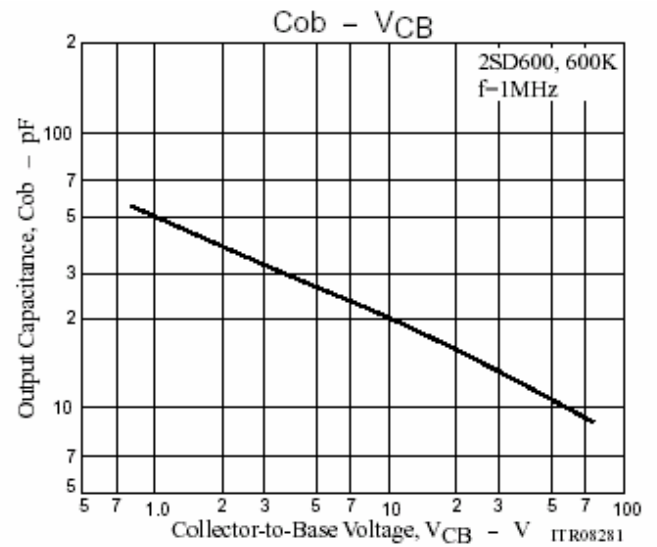
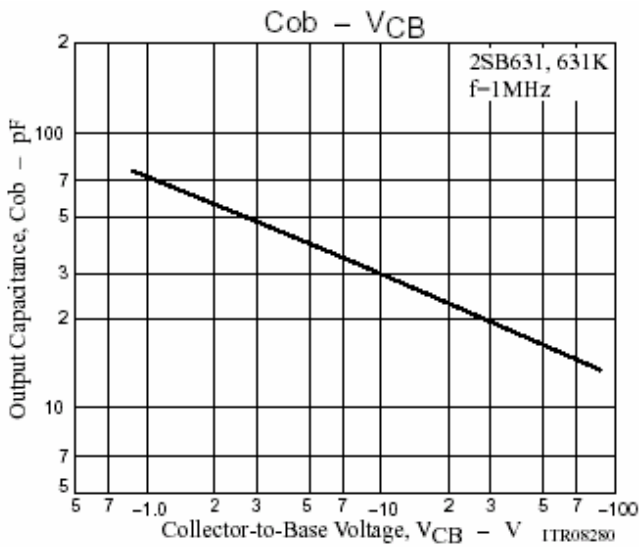
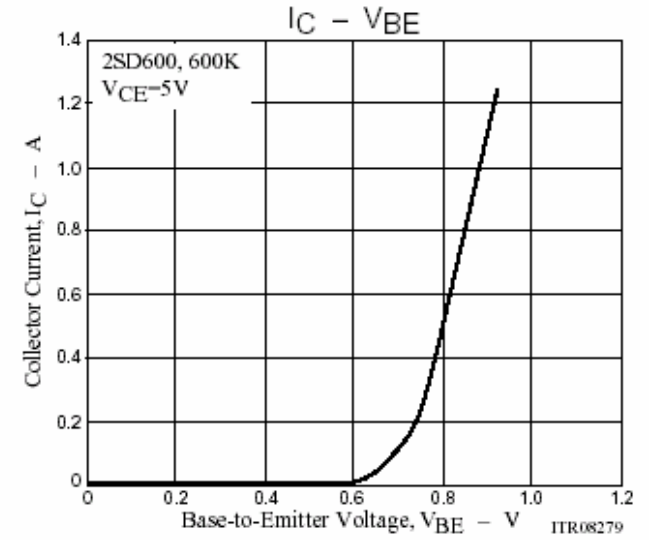
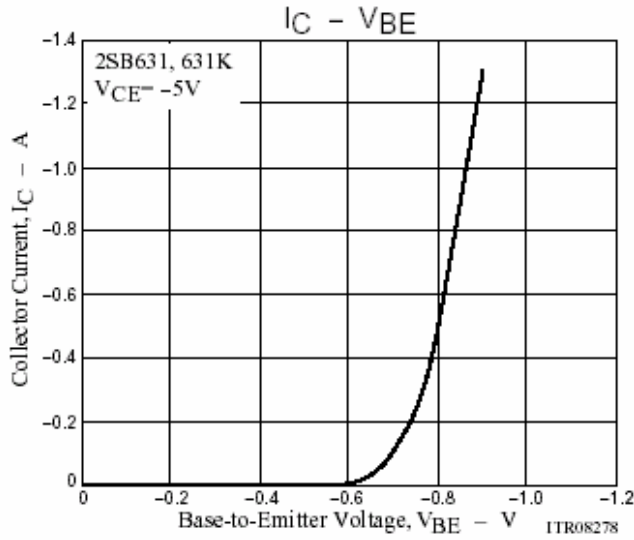
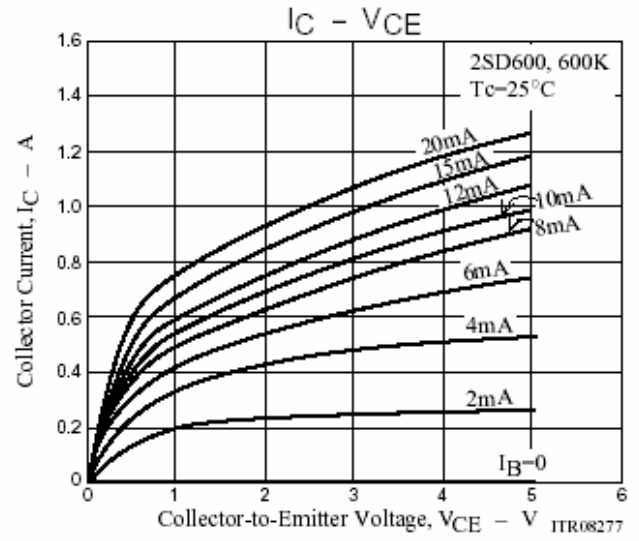
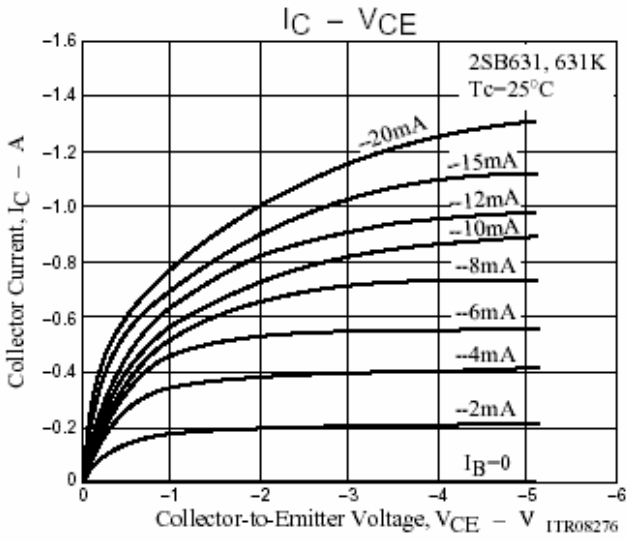
Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	-120			V	I _C =-10 μ A, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	-120			V	I _C =-1mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	-5			V	I _E =-10 μ A, I _C =0
I _{CB0}	Collector Cut-off Current			-1	μ A	V _{CB} =-50V, I _E =0
I _{EBO}	Emitter Cut-off Current			-1	μ A	V _{EB} =-4V, I _C =0
H _{FE} (1)	DC Current Gain	60		320		V _{CE} =-5V, I _C =-50mA
H _{FE} (2)	DC Current Gain	20				V _{CE} =-5V, I _C =-500mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage		-0.15	-0.4	V	I _C =-500mA, I _B =-50mA
V _{BE(sat)}	Base-Emitter Saturation Voltage		-0.85	-1.2	V	I _C =-500mA, I _B =-50mA
t _{OFF}	Turn-Off Time		100		nS	} See specified test circuit
t _{STG}	Storage Time		600		nS	
t _F	Fall Time		80		nS	
f _t	Current Gain-Bandwidth Product		110		MHz	V _{CE} =-10V, I _C =-50mA,
C _{ob}	Output Capacitance		30		pF	V _{CB} =10V, I _E =0, f=1MHz

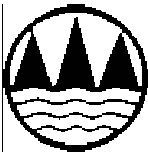
h_{FE} Classification

D	E	F
60—120	100—200	160—320



HS631K





HS631K

